



YJJ05N06AQ

N-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	60V
I_D	5.0A
$R_{DS(on)}$ (at $V_{GS}=10V$)	43m
$R_{DS(on)}$ (at $V_{GS}=4.5V$)	47m

General Description

Low $R_{DS(on)}$ & FOM
Extremely low switching loss

Epoxy Meets UL 94 V-0 Flammability Rating
-Q101 qualified

Halogen Free

Applications

Absolute Maximum Ratings ($T_A=25$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	60	V
Gate-source Voltage		V_{GS}	± 20	V
Drain Current	$T_A=25$	I_D	5	A
	$T_A=100$		3	
Pulsed Drain Current ^A		I_{DM}	20	A
Total Power Dissipation ^C	$T_A=25$	P_D	1.25	W
	$T_A=100$		0.5	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 +150	

Thermal resistance

Parameter		Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient ^D	Steady-State	R_{JA}	80	100	$^{\circ}W$

YJJ

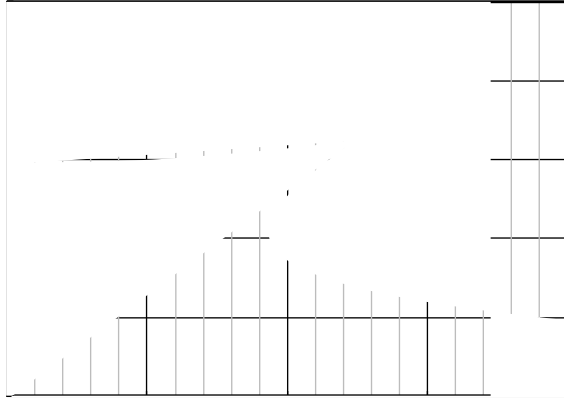


Figure 7. $R_{DS(on)}$ VS Drain Current

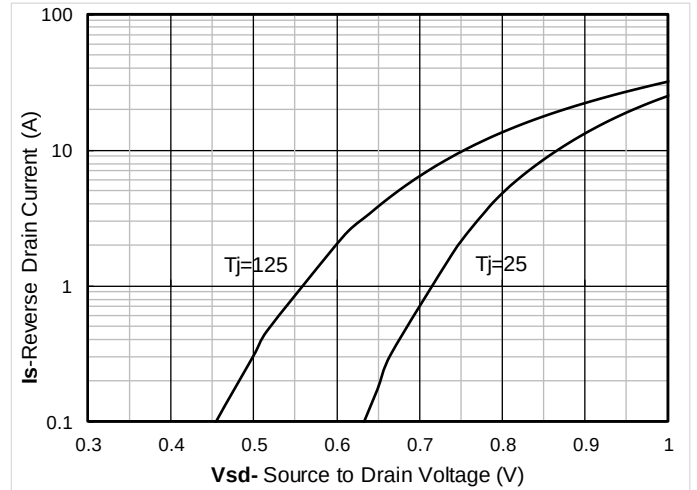


Figure 8. Forward characteristics of reverse diode

Figure 9. Normalized breakdown voltage

Figure 10. Normalized Threshold voltage

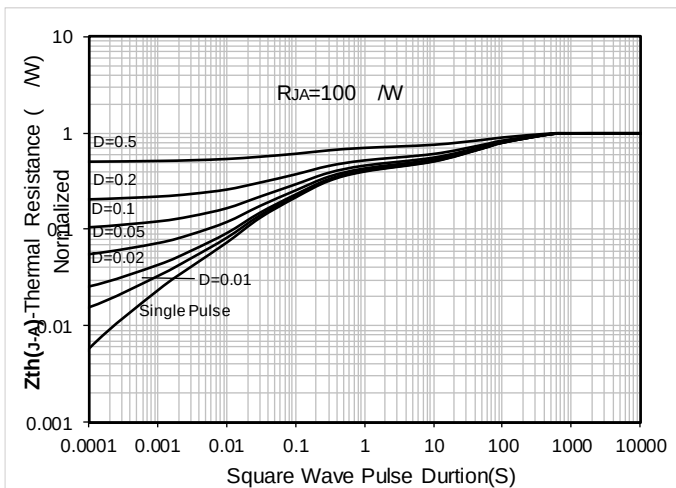


Figure 11. Maximum Transient Thermal Impedance

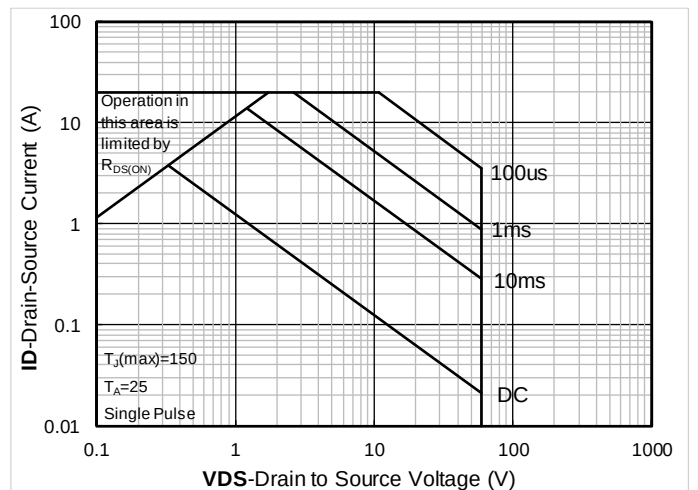
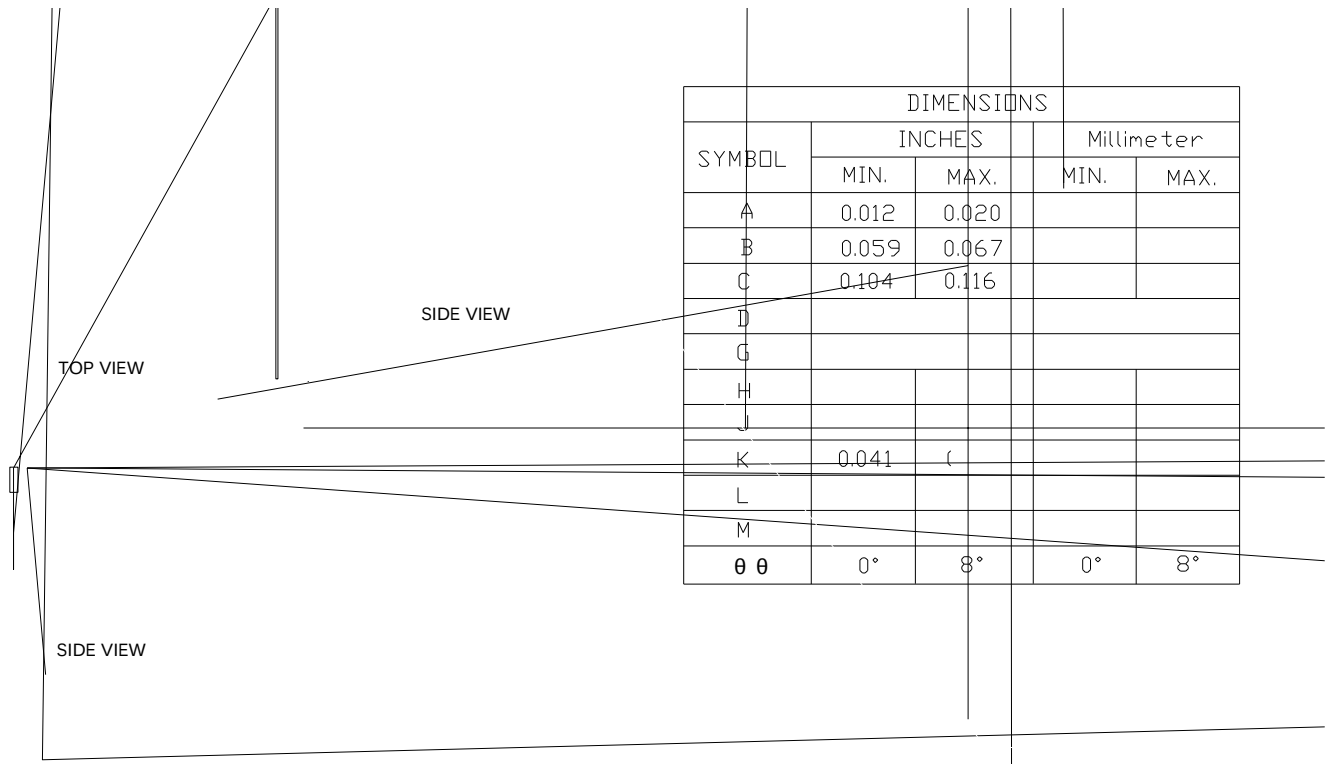


Figure 12. Safe Operation Area



SOT-23-6L Package information





Disclaimer

The information presented in this document is for reference only. Yangzhou Yangjie Electronic Technology Co., Ltd. reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise.

The product listed herein is designed to be used with automotive electronics are not designed for use in medical, life-saving, lifesustaining, or military, Yangjie or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale.

This publication supersedes & replaces all information previously supplied. For additional information, please visit our website <http://www.21yangjie.com>